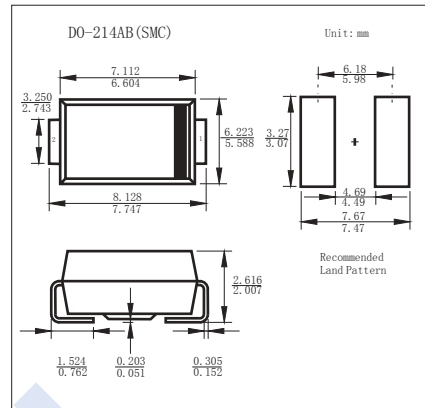


## Schottky Diodes

### 1N5820 ~ 1N5822

#### ■ Features

- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High surge capability
- Guardring for overvoltage protection



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	1N5820	1N5821	1N5822	Unit
Repetitive Peak Reverse Voltage	VRRM	20	30	40	V
RMS Voltage	VRMS	14	21	28	
Non-Repetitive Peak Reverse Voltage	VRSM	24	36	48	
Maximum DC Blocking Voltage	VDC	20	30	40	
Maximum Instantaneous Forward Voltage at 3.0 *1	VF	475	500	525	mV
Maximum Instantaneous Forward Voltage at 9.4 *1		850	900	950	
Averaged Forward Current.TL=95°C	IFAV	3			A
Peak Forward Surge Current TL=75°C	IFSM	80			
Maximum DC Reverse Current Ta=25°C *1	IR	2			mA
Ta=100°C		20			
Thermal Resistance From Junction to Ambient	RθJA	40			°C/W
Thermal Resistance From Junction to Lead	RθJL	10			
Junction Temperature	Tj	125			°C
Storage Temperature	Tstg	-65 to 125			

\*1:Pulse test: 300ms pulse width, 1% duty cycle

#### ■ Marking

NO.	1N5820	1N5821	1N5822
Marking	SS32	SS33	SS34

# Schottky Diodes

## 1N5820 ~ 1N5822

■ Typical Characteristics

FIG. 1 - FORWARD CURRENT DERATING CURVE

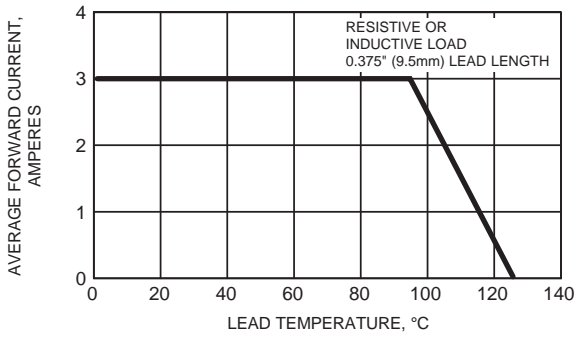


FIG. 2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

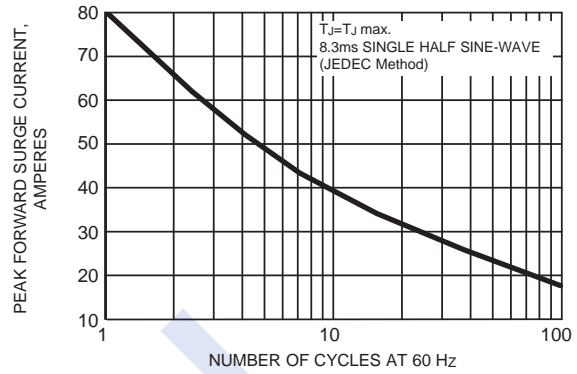


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

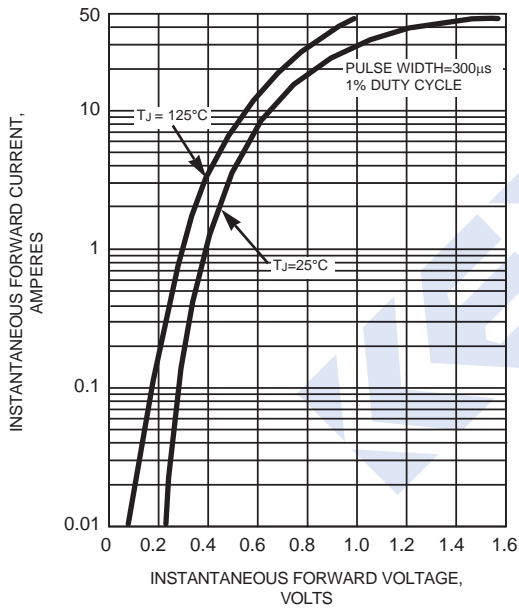


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS

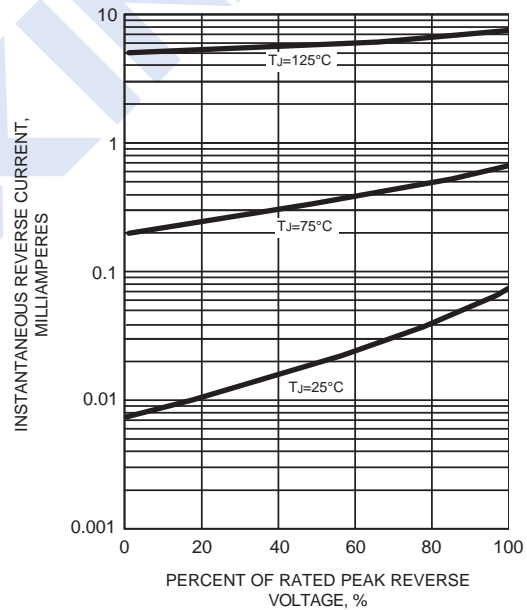


FIG. 5 - TYPICAL JUNCTION CAPACITANCE

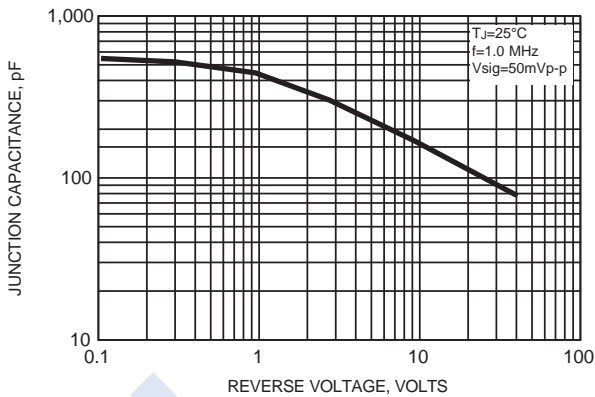


FIG. 6 - TYPICAL TRANSIENT THERMAL IMPEDANCE

